

In the Specification

Please replace the abstract with the following new abstract:

A method of forming a shared global word line MRAM structure is disclosed. The method includes, etching a trench in an oxide layer formed over a substrate, depositing an first liner material, anisotropically etching the deposited first liner material leaving the first liner material on edges of the trench and physically contacting a bottom of the trench, depositing an magnetic metal liner material, anisotropically etching the deposited magnetic metal liner material leaving the magnetic metal liner material over the first liner material on edges of the trench, so that the magnetic metal liner extends to and physically contacts the bottom of the trench, depositing a conductive layer,, and chemically, mechanically polishing the conductive layer.

Please replace the title with the following new title:

“A Method of Forming A Shared Global Word Line MRAM Structure”